(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

G00001

(43) International Publication Date
10 May 2002 (10.05.2002)

PCT

(10) International Publication Number
WO 02/37550 A1

(51) International Patent Classification[7]: H01L 21/336, 29/788, 29/792

(21) International Application Number: PCT/US01/24677

(22) International Filing Date: 6 August 2001 (06 08 2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/699,972 30 October 2000 (30.10.2000) US

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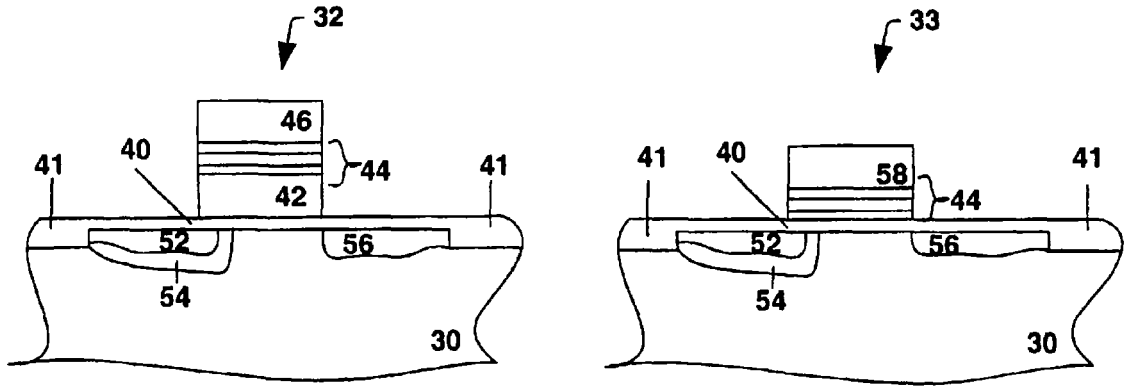
(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Published:
— with international search report
— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette

(54) Title: NON-VOLATILE MEMORY WITH SOURCE SIDE BORON IMPLANTATION



(57) Abstract: One aspect of the present invention relates to a method of making a flash memory cell (32) involving the steps of providing a substrate (30) having a flash memory cell (32) thereon, forming a self-aligned source mask (48) over the substrate (30), the self aligned source mask (48) having openings (50) corresponding to source lines, implanting a source dopant of a first type (52) in the substrate (30) through the openings (50) in the self-aligned source mask (48) corresponding to source lines; removing the self-aligned source mask (48) from the substrate (30), cleaning the substrate (30), and implanting a medium dosage drain implant of a second type to form a source region (54) and a drain region (56) in the substrate (30) adjacent the flash memory cell (32)

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